

a pressure detecting means provided inside said upper electrode, wherein
operation of said parallel-plate dry-etching apparatus ceases if a pressure measured by
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said pressure detecting means is lower than a predetermined value.

5. (Twice Amended) An apparatus for manufacturing a semiconductor device,
comprising:

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an upper electrode that supplies gas in a parallel-plate dry etching apparatus;
a first pressure detecting means provided inside of said upper electrode;
a second pressure detecting means provided within said dry etching apparatus in
which a wafer is placed; and
a detecting means which measures a pressure differential between respective
pressures of said first and said second pressure detecting means, and upon reaching a
predetermined pressure differential, operation of the apparatus is terminated.

REMARKS

Status of the Claims

Upon entry of the present amendment, claims 1-9 will be pending in this
application. Claims 3 and 5 are the independent claims.

Objection to the Drawings

The proposed amendment to Fig. 2 in red ink is believed to bring it in compliance
with MPEP § 608.02(g). A similar amendment was submitted on July 15, 2002.
Apparently this was not satisfactory. In the event that the present proposed changes are